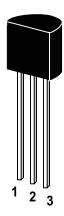
NPN Silicon Epitaxial Planar Transistor

for general purpose applications.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Base 3. Collector

TO-92 Plastic Package Weight approx. 0.19g

Absolute Maximum Ratings (T_a = 25 °C)

	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	50	V
Collector Emitter Voltage	V_{CEO}	30	V
Emitter Base Voltage	V _{EBO}	5	V
Collector Current	Ic	600	mA
Power Dissipation	P _{tot}	625	mW
Junction Temperature	T _j	150	$^{\circ}\!\mathbb{C}$
Storage Temperature Range	Ts	-55 to +150	$^{\circ}$







ST 2N3704

Characteristics at T_{amb} =25 $^{\circ}{\mathbb{C}}$

	Symbol	Min.	Тур.	Max.	Unit
DC Current Gain					
at V _{CE} =2V, I _C =50mA	*h _{FE}	100	-	300	-
Collector Base Breakdown Voltage					
at I _C =100μA	BV_CBO	50	-	-	V
Collector Emitter Breakdown Voltage					
at I _C =10mA	*BV _{CEO}	30	-	-	V
Emitter Base Breakdown Voltage					
at I _E =100μA	BV_{EBO}	5	-	-	V
Collector Cutoff Current					
at V _{CB} =20V	I _{CBO}	-	-	100	nA
Emitter Cutoff Current					
at V _{BE} =3V	I _{EBO}	-	-	100	nA
Output Capacitance					
at V _{CB} =10V, f=1MHz	Cob	-	-	12	pF
Collector Emitter Saturation Voltage					
at I _C =100mA, I _B =5mA	*V _{CE(sat)}	-	-	0.6	V
Base Emitter On Voltage					
at V _{CE} =2V, I _C =100mA	$*V_{BE(on)}$	0.5	-	1	V
Current Gain Bandwidth Product					
at V _{CE} =2V, I _C =50mA, f=20MHz	f _T	100		-	MHz

^{*} Pulse Test: Pulse Width≤300µs, Duty Cycle≤2%.





